

In the Specification:

Please add a new heading and a new paragraph at page 1, above line 5, as follows:

Priority Claim

This application is a 35 USC 371 National Stage of PCT International Application PCT/JP2004/005649 filed on April 20, 2004, and claims the foreign priority under 35 USC 119 of Japanese Patent Application 2003-122240 filed on April 25, 2003.

Please replace the paragraph at page 2, lines 10 to 15, with a replacement paragraph amended as follows:

When a ~~SiC-based~~ Si-based semiconductor substrate is used to fabricate a semiconductor device, p dopant and n dopant are selectively introduced through a single mask selectively and are thermally diffused to implement precise channel density. More specifically, JFET and similar semiconductor devices have characteristics depending on the channel's dimensions, which can significantly precisely be controlled, and increased yield of JFET or similar semiconductor devices can be achieved.

Please replace the paragraph at page 8, lines 20 to 26, with a replacement paragraph amended as follows:

Polyimide is a condensation polymer composed of bifunctional carboxylic anhydride and primary diamine and having an imide structure ($-\text{CO}-\text{NR}-\text{CO}$) at a main chain of a polymer skeleton. Of polyimides, aromatic heterocyclic polyimide is preferable as it has an excellent physical property and ~~significantly stable~~ has significant stability against heat and oxidation. Furthermore, of aromatic heterocyclic polyimides, a polyimide derived from aromatic diamine and aromatic dianhydride is more preferable as it is stable against heat.

Please replace the paragraph at page 10, lines 3 to 7, with a replacement paragraph amended as follows:

Preferably the thin film formed for example of SiO_2 is provided on the SiC semiconductor substrate before the polyimide resin film is provided, and after the polyimide resin film is exposed, developed and fired the thin film that is located in an opening of the polyimide resin film is wet etched away. Ion implantation is not prevented by the thin film and can ~~proceeds~~ proceed smoothly.